

SB5100U SCHOTTKY RECTIFIER

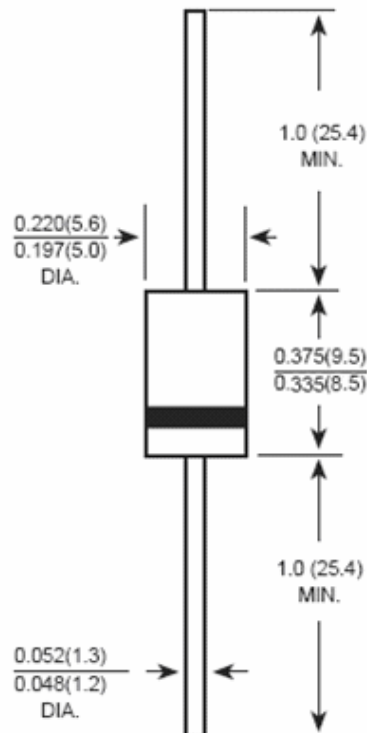
Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Disk drives
- Battery charging

Features:

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In Inches / mm



DO-201AD



Technical Data
Data Sheet N0881, Rev. A

Green Products

Marking Diagram:



Where XXXXX is YYWWL

- SB = Device Type
- 5 = Forward Current (5A)
- 100 = Reverse Voltage (100V)
- U = U
- SSG = SSG
- YY = Year
- WW = Week
- L = Lot Number

Cautions : Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
SB5100U	DO-201AD (Pb-Free)	1250 pcs / tape

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.



Maximum Ratings and Electrical Characteristics @ $T_A=25^{\circ}\text{C}$ unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

Characteristic	Symbol	MAX	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	100	V
Maximum RMS Voltage	V_{RMS}	70	V
Average Rectified Output Current (Note 1) @ $T_A = 80^{\circ}\text{C}$	$I_{F(AV)}$	5.0	A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	120	A
Forward Voltage @ $I_F = 5.0\text{A}, T_A = 25^{\circ}\text{C}$ @ $I_F = 5.0\text{A}, T_A = 125^{\circ}\text{C}$	V_{FM}	0.82 0.67	V
Peak Reverse Current At Rated DC Blocking Voltage @ $T_A = 25^{\circ}\text{C}$ @ $T_A = 125^{\circ}\text{C}$	I_{RM}	0.5 10	mA
Maximum Junction Capacitance (Note 2)	C_j	250	pF
Typical Thermal Resistance Junction to Ambient	$R_{\theta JA}$	25	K/W
Junction Temperature Range	T_J	-55 to +150	$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-55 to +150	$^{\circ}\text{C}$
Approximate Weight	wt	1.02	g
Case Style	DO-201AD		

Note:1. Leads maintained at ambient temperature at a distance of 9.5mm from the case.

2. Measured at 1MHz and applied reverse voltage of 5.0V D.C.

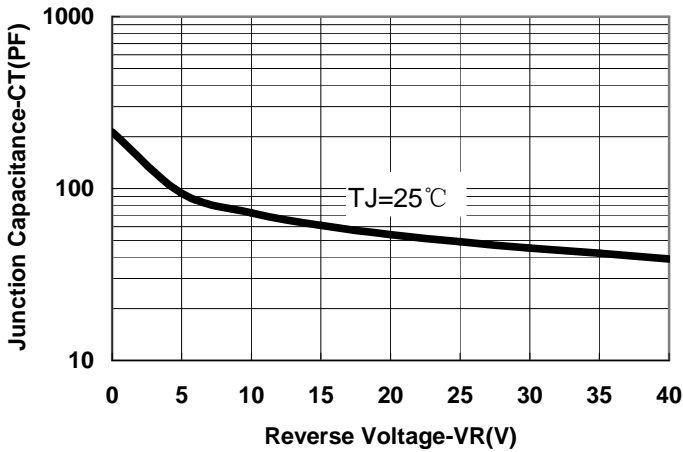


Fig.1-Typical Junction Capacitance Vs.Reverse Voltage

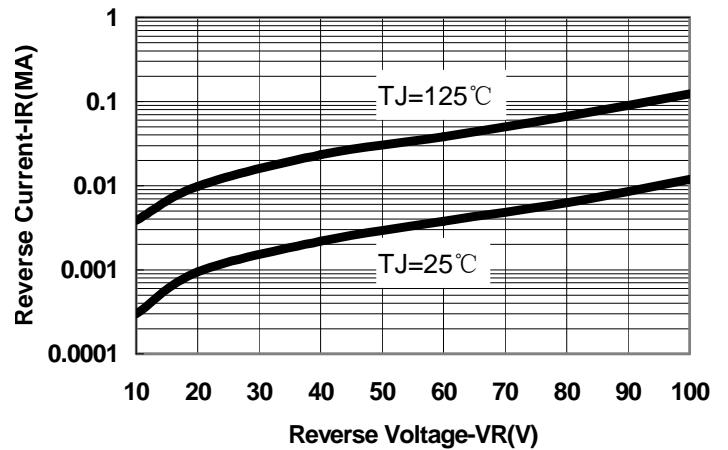


Fig.2-Typical Values Of Reverse Current Vs.Reverse Voltage

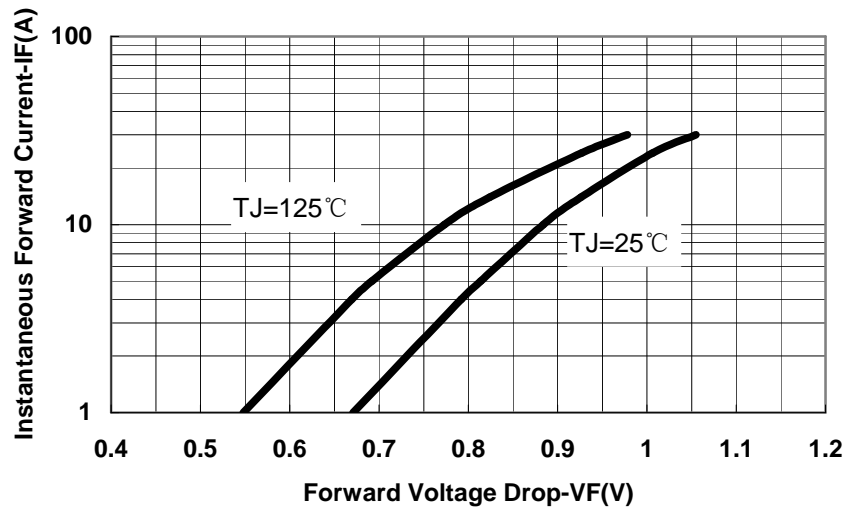


Fig.3-Typical Forward Voltage Drop Characteristics



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